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JAN 2 4 2006

SCULLY, SCOTT, MURPHY & PRESSER, P.C.



To:	Examiner Fernando L. Toledo Art Unit: 2823	From:	Leslie S. Szivos	
Fax:	571-273-8300	Pages:	12 pages (including	fax cover)
Phone:		Date:	January 24, 2006	
Re:	Hussein I. Hanafi et al. U.S. Patent Appln. No. 10/659,949 Docket: YOR920020182US2 (15790A) Conf. No.: 5877	CC:		
□ <b>V</b> rg	ent x For Review □ Please Co	mment	□ Please Reply	☐ Please Recycle

### PATENT OFFICE DATE STAMP WILL ACKNOWLEDGE RECEIPT OF:

- 1. Transmittal of Response Under 37 C.F.R. 1.111 (in duplicate)
- 2. Response Under 37 C.F.R. 1.111 (7 pages)
- 3. Certificate of transmission by facsimile dated January 24, 2006
- 5. Authorization to charge IBM deposit account

If you have any questions concerning this facsimile please contact Vivian Henriquez at 516-742-4343. Thank you

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CERTIFICATE OF Applicant(s): Hussein I.	YO	Docket No. R920020182US2 (15790A)						
Application No. 10/659,949				Group Art Unit 2823				
Invention: LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATIVE OXIDE REMOVAL ETCH								
				:				
I hereby certify that this Response under 37 C.F.R. §§1.111 (Identify type of correspondence)								
on January 24	nitted to the United States Patent	and Hademark Office (Fax.	NO. <u>5</u>	11-2/3-6300				
		Leslie Ş. Sziv	os. Ph.	D				
		(Typed or Printed Nathelof)Per	Signi	ng Cerificate)				
	(Signature)							
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CERTIFICATE OF  Applicant(s): Hussein I.	VO	Docket No. R920020182US2 (15790A)						
Applicant(5). Itussem i.	10	1920020102052 (13790A)						
Application No.	Filing Date	Examiner		Group Art Unit				
10/659,949	September 11, 2003	Fermando L. Toledo	2823					
10/00>,>>	10/059,949 September 11, 2003 Fernando			2020				
Invention: LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE								
	AND AN INNOVATIVE OXIDE							
I MOCESS A	END AN INNOVATIVE CAIDE	REMOVAL EICH						
I hereby certify that this   Response under 37 C.F.R. \$81.111  (Identify type of correspondence)  is being facsimile transmitted to the United States Patent and Trademark Office (Fax. No. 571-273-8300  on January 24, 2006  (Date)  Leslie S. Salvey Ph.P.  (Typed or Printed Namy Lift Pelain Sigling Certificate)  (Signature)  Note: Each paper must have its own certificate of mailing.								

## JAN 2 4 2006

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AMENDMENT TRANSMITTAL LETTER (Large Entity) Applicant(s): Hussein I. Hanafi et al.					Docket No. YOR920020182US2 (15790A)		
Application No. 10/659,949	Filing Date September 11, 2003	Examiner Fernando L. Toled	lo	Customer No. 23389	Group Art Unit 2823	Confirmation No. 5877	
Invention: LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATIVE OXIDE REMOVAL ETHCH							
		COMMISSIONER FO					
		n the above-identified a mitted as shown below		on.			
		CLAIMS AS AM	ENDED	)			
	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST # PREV. PAID FOR		ER EXTRA	RATE	ADDITIONAL FEE	
TOTAL CLAIMS	9 -	20 =		0 x		\$0.00	
INDEP. CLAIMS	3 -	3 =		0 x		\$0.00	
Multiple Dependent Claims (check if applicable)							
		TOTAL ADDITIONAL F	FEE FO	R THIS AMEN	DMENT	\$0.00	
No additional fee is required for amendment.  □ Please charge Deposit Account No. in the amount of □ A check in the amount of to cover the filing fee is enclosed. □ The Director is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account 50-0510/IBM □ Any additional filing fees required under 37 C.F.R. 1.16. □ Any patent application processing fees under 37 CFR 1.17. □ Payment by credit card. Form PTO-2038.  WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.  Dated: January 24, 2006  Leslie S. Szivos, Ph.D.							
Registration No. 39, 394  I hereby certify that this correspondence is being deposited will the United States Postal Service with sufficient postage as find class mail in an envelope addressed to "Commissioner for Patents P.O. Box 1450, Alexandria, VA 22313-1450" [37 CFR 1.8(a)] on  (Date)  Signature of Person Mailing Correspondence cc:						clent postage as first prissioner for Patents, [37 CFR 1.8(a)] on	
Typed or Printed Name of Person Mailing Correspondence							

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AMENDMENT TRANSMITTAL LETTER (Large Entity) Applicant(s): Hussein I. Hanafi et al.				Docket No. YOR920020182US2 (15790A)			
Application No.	Filing Date	Examiner		Customer No	. Group Art Unit	Confirmation No.	
10/659,949	September 11, 2003	Fernando L. Toled	lo	23389	2823	5877	
Invention: LOW RESISTANCE T-GATE MOSFET DEVICE USING A DAMASCENE GATE PROCESS AND AN INNOVATIVE OXIDE REMOVAL ETHCH							
		COMMISSIONER FO	R PAT	ENTS:		_	
Transmitted herew	ith is an amendment i	n the above-identified a	pplication	on.			
The fee has been o	calculated and is trans	mitted as shown below.	•				
		CLAIMS AS AM	ENDEC	)			
	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST # PREV. PAID FOR		ER EXTRA S PRESENT	RATE	ADDITIONAL FEE	
TOTAL CLAIMS	9 -	20 =		0 x		\$0.00	
INDEP. CLAIMS	3 -	3 =		0 x		\$0.00	
Multiple Dependent Claims (check if applicable)  \$0.00							
		TOTAL ADDITIONAL F	EE FO	R THIS AME	IDMENT	\$0.00	
No additional fee is required for amendment.  □ Please charge Deposit Account No. In the amount of □ A check in the amount of to cover the filling fee is enclosed.  □ The Director is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account 50-0510/IBM □ Any additional filling fees required under 37 C.F.R. 1.16. □ Any patent application processing fees under 37 CFR 1.17. □ Payment by credit card. Form PTO-2038.  WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.  Leslie S. Szivos, Ph.D.							
Registration No. 39, 394  I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to "Compossioner for Patents. P.O. Box 1450, Alexandria, VA 22313-1458" [37 CFR 1.8(a)] on  (Date)  LSS:vh  CC:  Typed or Printed Name of Person Mailing Correspondence							

JAN 2 4 2006

### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Hussein I. Hanafi et al.

Docket:

YOR920020182US2

(15790A)

Serial No.:

10/659,949

Examiner:

Fernando L. Toldeo

Filed:

September 11, 2003

Art Unit:

2823

For:

LOW RESISTANCE T-GATE

Dated:

January 24, 2006

MC

MOSFET DEVICE USING A

DAMASCENE GATE PROCESS

AND AN INNOVATIVE OXIDE

REMOVAL ETCH

Confirmation No:

5877

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

#### RESPONSE UNDER 37 C.F.R. § 1.111

Sir:

In response to the Office Action dated October 31, 2005, applicants submit the following amendments and remarks for entry of record in the above-identified patent application.

#### **CERTIFICATION OF FACSIMILE TRANSMISSION**

I hereby certify that this paper is being facsimile transmitted to the Patent and Trademark Office on the date shown below.

Dated: January 24, 2006

Leslie S. Szivos